

5 é / Descriptions

SOD-323 .> // x J ' ! - } 8 â ' ož
Silicon Diode in a SOD-323 Plastic Package.

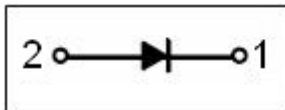
¤ ª / Features

• ¼ , † ½ ož —) í D } ož
Fast switching diodes. HF Product.

Đ ÷ / Applications

9 4 ' Z Ô ò ož
Small signal diode.

Ã W] Ô . / Equivalent Circuit



• Ū - æ / Pinning



PIN1:Cathode PIN2:Anode

Z Ü B , M V / h_{FE} Classifications & Marking

Marking	HA2
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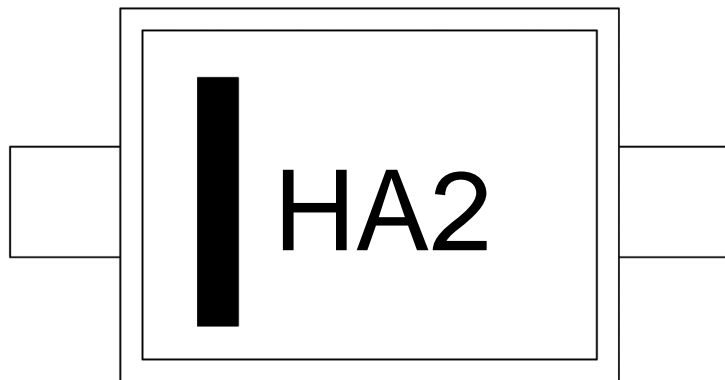
@ f Parameter	... Z Symbol	f › Rating	% y Unit
Reverse Voltage	V_R	75	V
Peak Reverse Voltage	V_{RM}	100	V
Average Rectified Output Current	I_O	150	mA
Forward Continuous Current	I_{FM}	300	mA
Non-Repetitive Peak Forward Surge Current	$I_{FSM} \text{ } \ddot{A}t=1.0 \text{ s } \ddot{A}$	2.0	A
	$I_{FSM} \text{ } \ddot{A}t=1.0\text{s } \ddot{A}$	1.0	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	
Thermal Resistance Junction to Ambient Air	R_{JA}	625	/W

@ f Parameter	... Z Symbol	y j Ú ^ Test Conditions	Â 4 › Min	Â ° › Typ	Â Ý › Max	% y Unit
Forward Voltage	V_F	$I_F=10\text{mA}$			1.0	V
Instantaneous Reverse Current	I_R	$V_R=20\text{V}$			25	nA
		$V_R=75\text{V}$			5	A
		$V_R=20\text{V} \quad T_j=150$			50	A
Capacitance	C_{tot}	$V_F=V_R=0\text{V}$			4	pF
Reverse Recovery Time	t_{rr}	$I_F=10\text{mA} \quad V_R=6.0\text{V}$ $I_R=1\text{mA} \quad R_L=100$			4	ns
Voltage Rise when Switching On tested	V_{fr}	$t_p=0.1 \text{ s} \quad f_p=5\text{to}100\text{kHz}$ Time<30ns			2.5	V
Total Capacitance	C_T	$V_R=0 \quad f=1.0\text{MHz}$			2.0	pF

Electrical Characteristic Curve



, M y f / Marking Instructions



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Note:

H: Company Code.

A2: Product Type.

